

BS IEC 61435:2013



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**Nuclear instrumentation —
High-purity germanium
crystals for radiation
detectors — Measurement
methods of basic
characteristics**

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National foreword

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The UK participation in its preparation was entrusted to Technical Committee NCE/2, Radiation protection and measurement.

A list of organizations represented on this committee can be obtained on request to its secretary.

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Nuclear instrumentation – High-purity germanium crystals for radiation detectors – Measurement methods of basic characteristics

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ELECTROTECHNICAL
COMMISSION

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

NUCLEAR INSTRUMENTATION – HIGH-PURITY GERMANIUM CRYSTALS FOR RADIATION DETECTORS – MEASUREMENT METHODS OF BASIC CHARACTERISTICS

FOREWORD

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International Standard IEC 61435 has been prepared by IEC technical committee 45: Nuclear instrumentation.

This second edition cancels and replaces the first edition published in 1996 and constitutes a technical revision.

The main technical changes with regard to the previous edition are as follows:

- Review the existing requirements.
- Update the terminology and definitions.

The text of this standard is based on the following documents:

FDIS	Report on voting
45/754/FDIS	45/760/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

INTRODUCTION

Detector manufacturers demand numerical data that can be used to predict the performance of a detector having approximately coaxial geometry. However, because of the many variations in the physical characteristics, the completed detector performance cannot be fully predicted from measurements of the crystal manufacturer. This standard defines terminology and test methods for determining basic crystal parameters such as net electrically active impurity concentrations, deep-level impurity-centre concentration and crystallographic quality of crystals.

Production of germanium crystals of the necessary size and defined purity for high-purity germanium (HPGe) detectors for detection of ionizing radiation has special problems in characterization resulting from the high resistivity of the material ($\sim 10 \text{ k}\Omega\cdot\text{cm}$ at 77 K), from the degree of impurity compensation, and from difficulties in suitably describing the impurity distribution in the large volume that may form a single device. Existing standards do not cover these problems.

One of the most important characteristics of HPGe is the net electrically active impurity concentration ($N_A - N_D$) because it determines the depletion voltage required for an operating detector. The usual practice has been to determine ($N_A - N_D$), with the sign indicating n-type or p-type, on the basis of transport measurements using the Van der Pauw method [1]¹ on lamellar samples immersed in liquid nitrogen (LN).

In this technique, ($N_A - N_D$) can be computed either from the resistivity or from the Hall coefficient. These in turn are obtained from a series of electrical measurements made on the sample.

¹ Numbers in square brackets refer to the Bibliography.

NUCLEAR INSTRUMENTATION – HIGH-PURITY GERMANIUM CRYSTALS FOR RADIATION DETECTORS – MEASUREMENT METHODS OF BASIC CHARACTERISTICS

1 Scope and object

This International Standard is applicable to high-purity germanium crystals used for radiation detectors for gamma-rays and X-rays. Such germanium is monocrystalline and has a net concentration of fewer than 10^{11} electrically active impurity centers per cm^3 , usually of the order of 10^{10} cm^{-3} .

This International Standard specifies terminology and test methods for measurements of basic characteristics of high-purity germanium crystals. These characteristics are net electrically active impurity concentrations (hereinafter $(N_A - N_D)$), deep-level impurity-centre concentration and crystallographic quality of crystals.

These test methods are not mandatory but have found general use in the industry and provide verifiable and desired information to the detector manufacturer.

Test methods for completed assembled germanium detectors are given in IEC 60973 and IEC 60759.

2 Normative references

The following documents, in whole or in part, are normatively referenced in this document and are indispensable for its application. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 600050-393:2003, *International Electrotechnical Vocabulary (IEV) – Part 393: Nuclear instrumentation – Physical phenomena and basic concepts*

IEC 60050-394:2007, *International Electrotechnical Vocabulary (IEV) – Part 394: Nuclear instrumentation – Instruments, systems, equipment, and detectors*

IEC 60050-521:2002, *International Electrotechnical Vocabulary (IEV) – Part 521: Semiconductor devices and integrated circuits*

3 Terms, definitions, symbols and abbreviations

3.1 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

3.1.1

semiconductor

substance whose total conductivity due to charge carriers of both signs is normally in the range between that of conductors and insulators and in which the charge carrier density can be changed by external means

Note 1 to entry: The term semiconductor generally applies where the charge carriers are electrons or holes.

[SOURCE: IEC 60050-521:2002, 521-02-01]